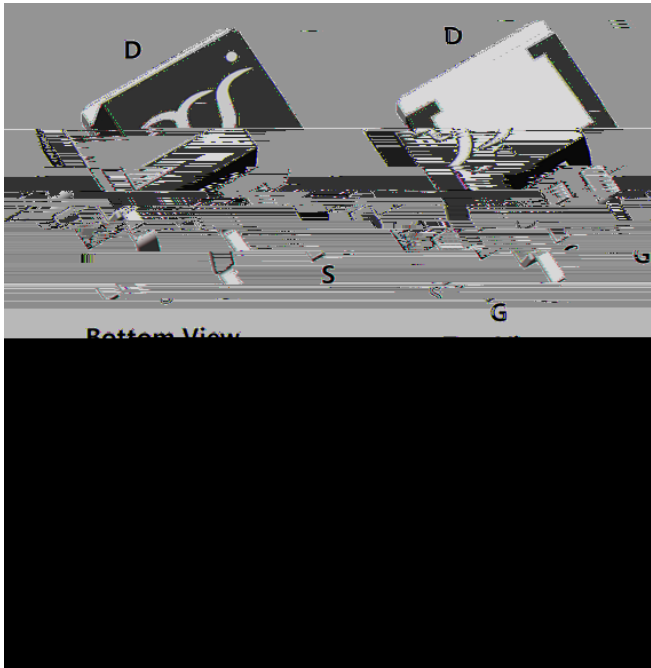




- $R_{DS(ON)}$ (at $V_{GS}=6V$)
5.5mohm
6.5mohm
- 100% EAS Tested
- 100% VDS Tested
- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free
- Power switching application
- Uninterruptible power supply
- DC-DC convertor

(T

	$T_A=25$		15		T
Drain Current		I_D		A	

Avalanche energy^B

Junction and Storage Temperature Range	T_J, T_{STG}	-55 +150	
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Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	35	45	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	0.55	0.7	

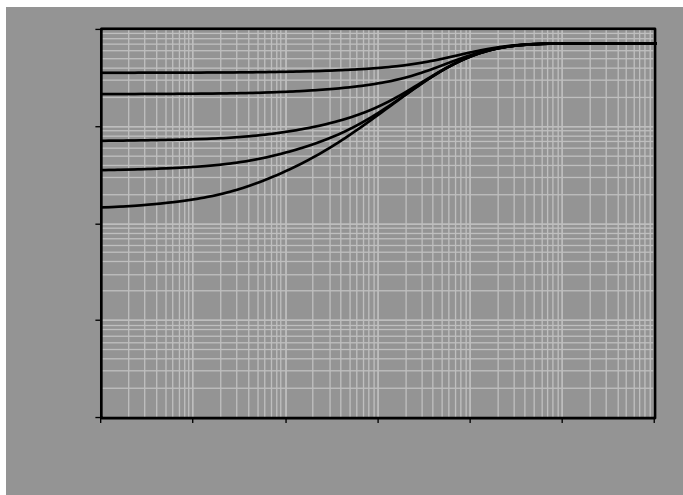
(Example)

YJB130G10B	F2	YJB130G10B	800	/	8000	13" reel
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■ (T_J=25 unless otherwise noted)

Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS}				





SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.010	0.000	---	0.250
A2	0.174	0.180	0.186	4.430	4.580	4.730
b	0.028	0.032	0.036	0.720	0.820	0.920
b2	0.046	0.050	0.054	1.180	1.280	1.380
c	0.013	0.015	0.018	0.330	0.390	0.450
c2	0.048	0.050	0.053	1.220	1.280	1.340
D1						
D2	0.303	0.315	0.327	7.700		8.300
E	0.571	0.591	0.610	14.500		15.500
E1	0.337	0.341	0.348	8.550		8.850
E2						
e	0.200BSC			5.080BSC		
L	0.070		0.110	1.790		2.790
L1						
L2	0.030		0.070	0.770		1.770
L3	0.197REF					
θ	0°		8°	0°		8°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

